

CGH35030F

30 W, 3.3-3.9 GHz, 28V, GaN HEMT for WiMAX

Description

WolfSpeed's CGH35030F is a gallium nitride (GaN) high electron mobility transistor (HEMT) designed specifically for high efficiency, high gain and wide bandwidth capabilities, which makes the CGH35030F ideal for 3.3-3.9 GHz WiMAX and BWA amplifier applications. The transistor is supplied in a ceramic/metal flange package.



Package Types: 440166
PN: CGH35030F

Typical Performance Over 3.3-3.8 GHz ($T_c = 25^\circ\text{C}$) of Demonstration Amplifier

Parameter	3.3 GHz	3.4 GHz	3.5 GHz	3.6 GHz	3.7 GHz	3.8 GHz	Units
Small Signal Gain	11.6	11.8	11.8	12.0	12.4	13.0	dB
EVM at $P_{AVE} = 23$ dBm	2.42	2.26	2.09	2.11	2.13	2.38	%
EVM at $P_{AVE} = 36$ dBm	1.97	1.74	1.68	1.79	2.01	2.37	%
Drain Efficiency @ 36 dBm	20.8	21.9	23.5	25.4	27.4	29.1	%
Input Return Loss	12.3	8.5	6.1	5.4	6.1	9.0	dB

Note:

Measured in the CGH35030F-AMP amplifier circuit, under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, 5ms Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01% Probability on CCDF.

Features

- 3.3 - 3.9 GHz Operation
- 30 W Peak Power Capability
- 12 dB Small Signal Gain
- 4.0 W $P_{AVE} < 2.0\%$ EVM
- 25% Efficiency at 4 W P_{AVE}
- WiMAX Fixed Access 802.16-2004 OFDM
- WiMAX Mobile Access 802.16e OFDMA

 Large Signal Models Available for ADS and MWO





Absolute Maximum Ratings (not simultaneous) at 25°C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	V_{DS}	120	V	25°C
Gate-to-Source Voltage	V_{GS}	-10, +2		
Power Dissipation	P_{DISS}	14	W	
Storage Temperature	T_{STG}	-65, +150	°C	
Operating Junction Temperature	T_J	225		
Maximum Forward Gate Current	I_{GMAX}	4.0	mA	25°C
Maximum Drain Current ¹	I_{DMAX}	3.0	A	
Soldering Temperature ²	T_S	245	°C	
Screw Torque	τ	40	in-oz	
Thermal Resistance, Junction to Case ³	$R_{\theta JC}$	4.8	°C/W	85°C
Case Operating Temperature ³	T_C	-40, +150	°C	

Notes:

¹ Current limit for long term, reliable operation

² Refer to the Application Note on soldering at wolfspeed.com/rf/document-library

³ Measured for the CGH35030F at $P_{DISS} = 14$ W.

Electrical Characteristics ($T_c = 25^\circ\text{C}$)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics¹						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	V_{DC}	$V_{DS} = 10$ V, $I_D = 7.2$ mA
Gate Quiescent Voltage	$V_{GS(Q)}$	–	-2.7	–		$V_{DS} = 28$ V, $I_D = 120$ mA
Saturated Drain Current	I_{DS}	5.8	7.0	–	A	$V_{DS} = 6.0$ V, $V_{GS} = 2$ V
Drain-Source Breakdown Voltage	V_{BR}	84	–	–	V_{DC}	$V_{GS} = -8$ V, $I_D = 7.2$ mA
RF Characteristics^{2,3} ($T_c = 25^\circ\text{C}$, $F_0 = 3.5$ GHz unless otherwise noted)						
Small Signal Gain	G_{SS}	10	11.5	–	dB	$V_{DD} = 28$ V, $I_{DQ} = 120$ mA, $P_{AVE} = 23$ dBm
Drain Efficiency ⁴	η	20	25	–		$V_{DD} = 28$ V, $I_{DQ} = 120$ mA, $P_{AVE} = 36$ dBm
Back-Off Error Vector Magnitude	EVM	–	2.5	–	%	$V_{DD} = 28$ V, $I_{DQ} = 120$ mA, $P_{AVE} = 23$ dBm
Error Vector Magnitude		–	2.0	–		$V_{DD} = 28$ V, $I_{DQ} = 120$ mA, $P_{AVE} = 36$ dBm
Output Mismatch Stress	VSWR	–	–	10:1	Ψ	No damage at all phase angles, $V_{DD} = 28$ V, $I_{DQ} = 120$ mA
Dynamic Characteristics						
Input Capacitance	C_{GS}	–	9.0	–	pF	$V_{DS} = 28$ V, $V_{GS} = -8$ V, $f = 1$ MHz
Output Capacitance	C_{DS}	–	2.6	–		
Feedback Capacitance	C_{GD}	–	0.4	–		

Notes:

¹ Measured on wafer prior to packaging.

² Measured in the CGH35030F-AMP test fixture

³ Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, 5ms Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01% Probability on CCDF

⁴ Drain Efficiency = P_{OUT} / P_{DC}



Typical WiMAX Performance

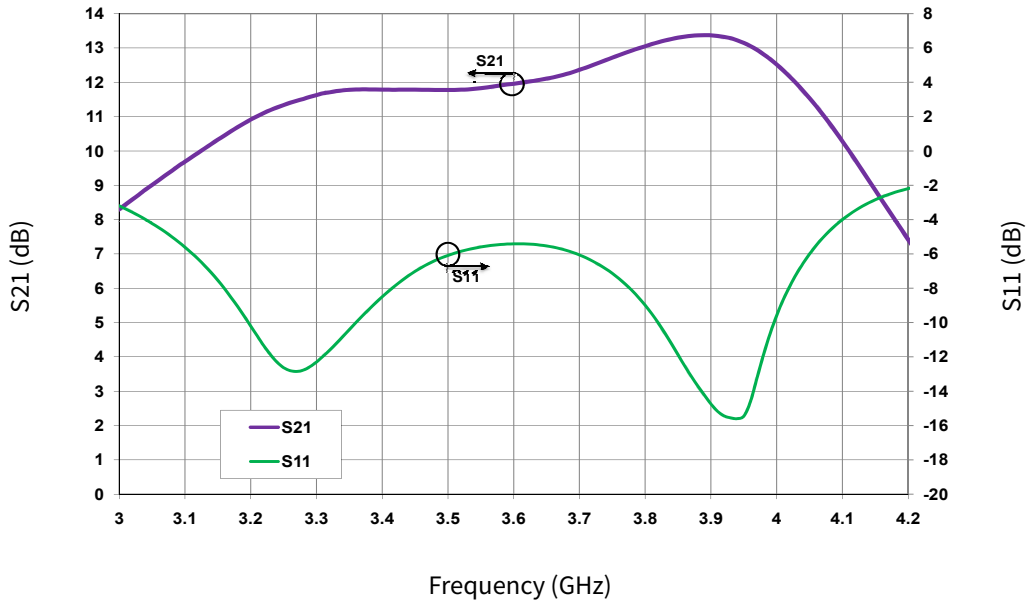


Figure 1. Gain and Return Loss vs Frequency measured in Broadband Amplifier Circuit CGH35030F-AMP
 $V_{DD} = 28\text{ V}$, $I_{DQ} = 120\text{ mA}$

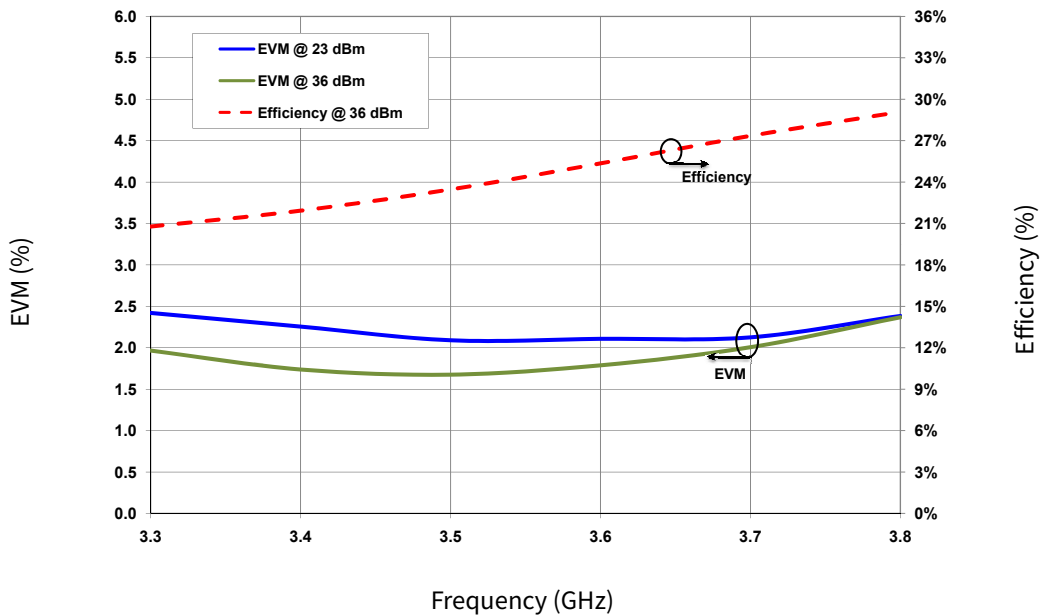


Figure 2. Typical EVM and Efficiency at 23 dBm and 36 dBm vs Frequency measured in Broadband Amplifier Circuit CGH35030F-AMP

Note:
¹ Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01% Probability on CCDF.



Typical WiMAX Performance

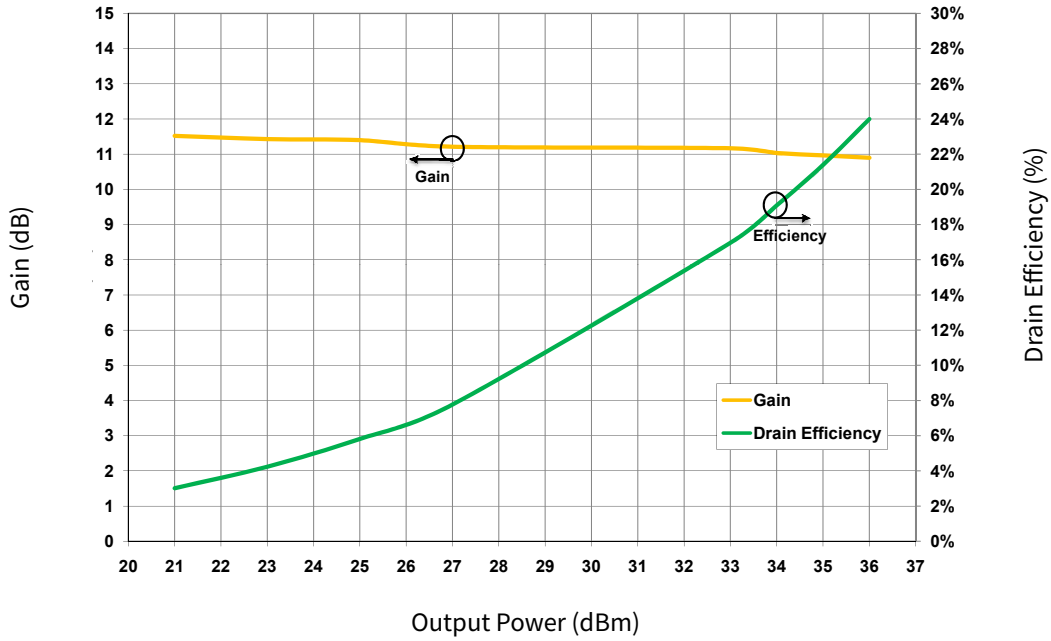


Figure 3. Gain and Return Loss vs Frequency measured in Broadband Amplifier Circuit CGH35030F-AMP
 $V_{DD} = 28\text{ V}$, $I_{DQ} = 120\text{ mA}$

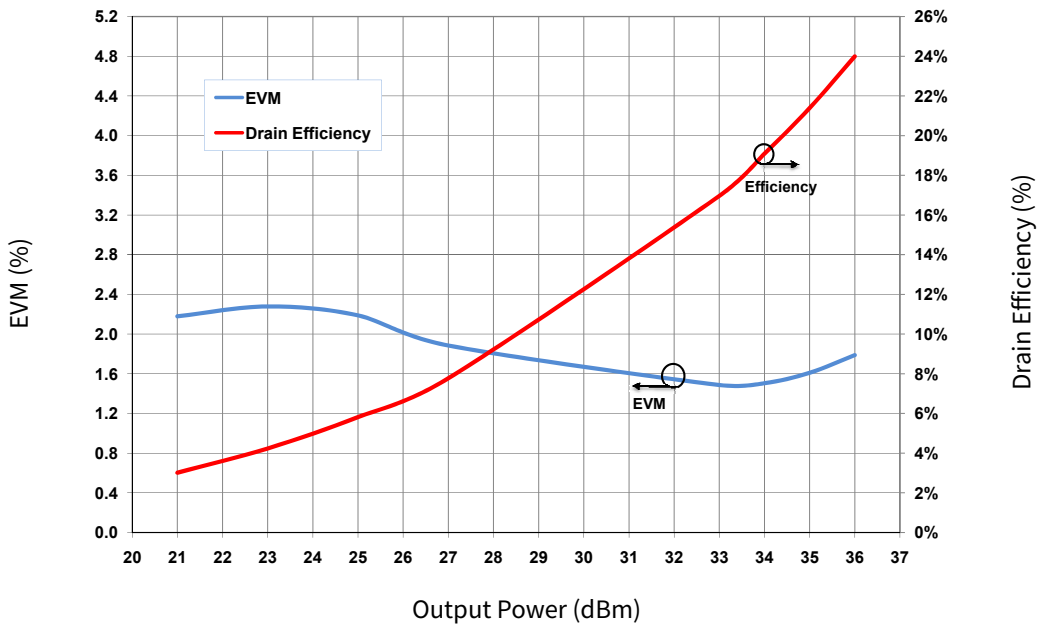


Figure 4. Typical EVM and Efficiency vs Frequency measured in Broadband Amplifier Circuit CGH35030F-AMP

Note:
¹ Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01% Probability on CCDF.



Typical Performance

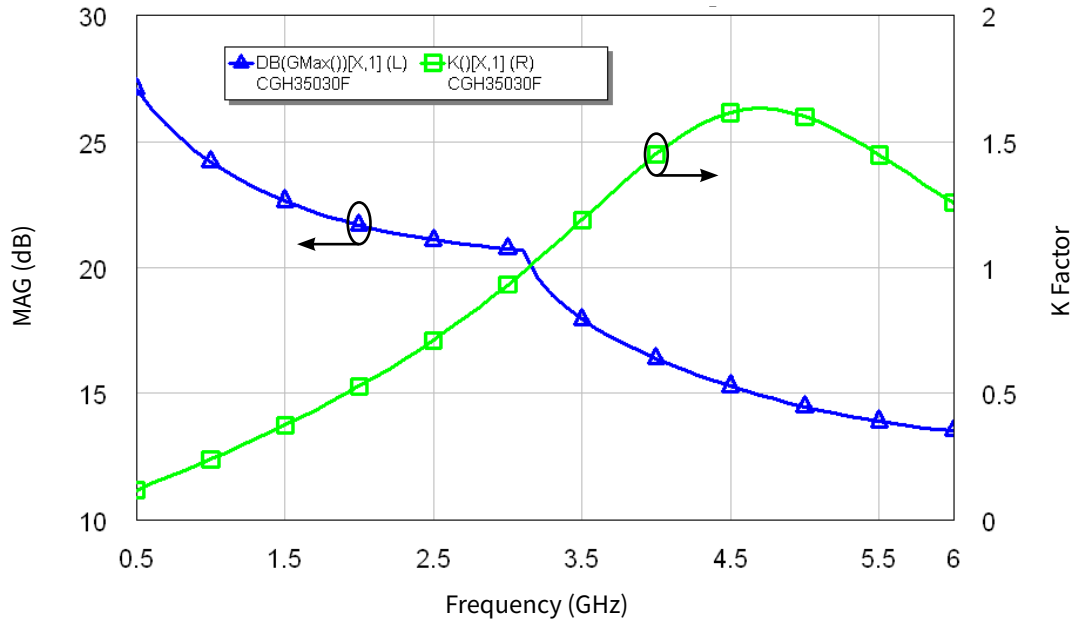


Figure 5. Simulated Maximum Available Gain and K Factor of the CGH35030F
 $V_{DD} = 28\text{ V}$, $I_{DQ} = 120\text{ mA}$

Typical Noise Performance

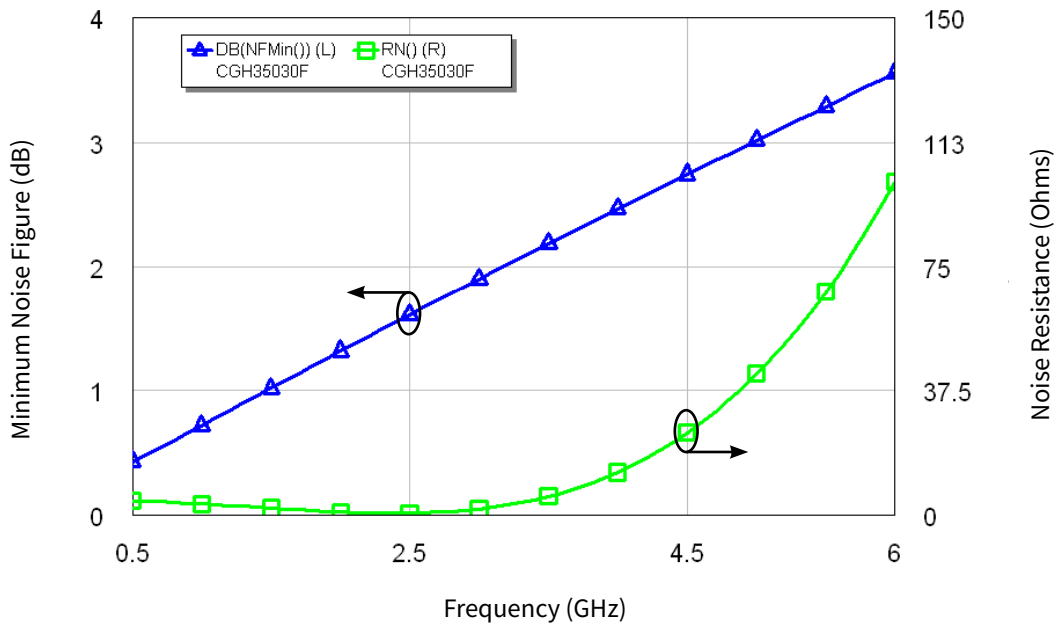
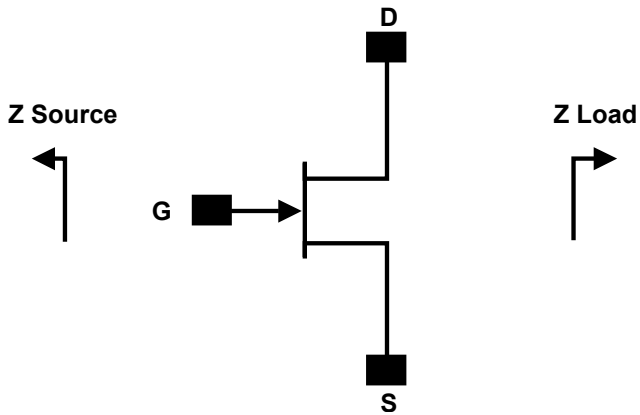


Figure 6. Simulated Minimum Noise Figure and Noise Resistance vs Frequency of the CGH35030F
 $V_{DD} = 28\text{ V}$, $I_{DQ} = 120\text{ mA}$



Source and Load Impedances



Frequency (MHz)	Z Source	Z Load
3300	3.3 - j9.2	13.4 - j11.4
3400	3.9 - j8.6	12.2 - j10.4
3500	4.5 - j8.5	11.1 - j9.4
3600	4.7 - j8.8	10.2 - j8.2
3700	4.3 - j9.0	9.5 - j7.1

Notes:

¹ $V_{DD} = 28V$, $I_{DQ} = 120mA$ in the 440166 package.

² Impedances are extracted from the CGH35030F-AMP demonstration amplifier and are not source and load pull data derived from the transistor.

Electrostatic Discharge (ESD) Classifications

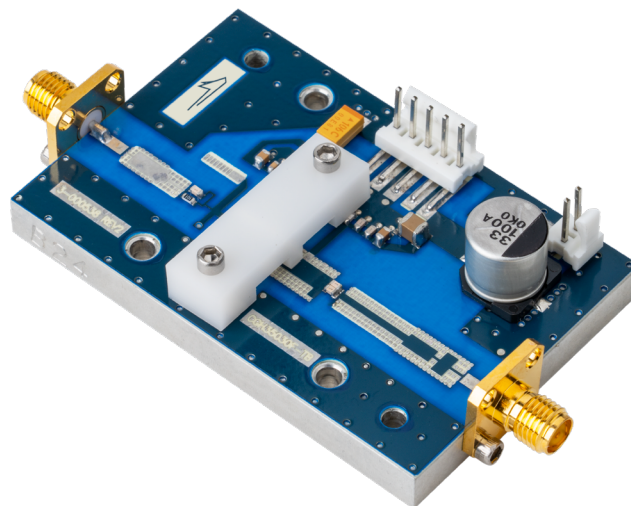
Parameter	Symbol	Class	Classification Level	Test Methodology
Human Body Model	HBM	TBD	ANSI/ESDA/JEDEC JS-001 Table 3	JEDEC JESD22 A114-D
Charge Device Model	CDM	TBD	ANSI/ESDA/JEDEC JS-002 Table 3	JEDEC JESD22 C101-C



CGH35030F-AMP Demonstration Amplifier Circuit Bill of Materials

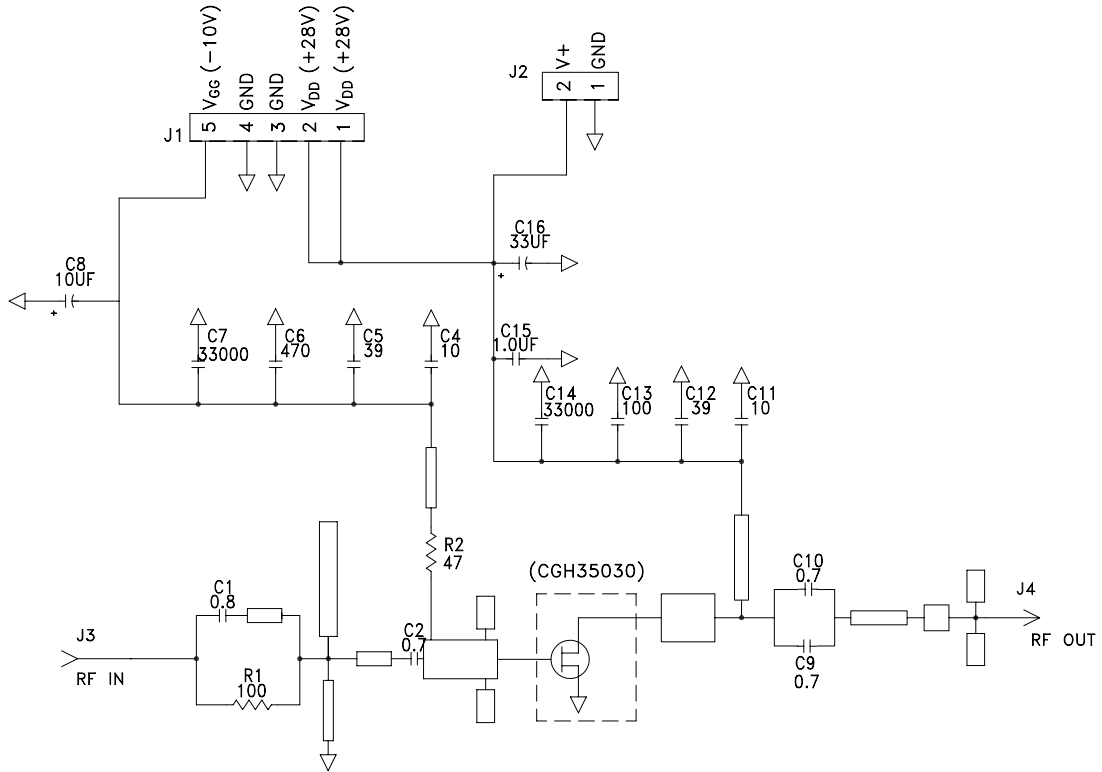
Designator	Description	Qty
R1	RES, 1/16W, 0603, 1%, 100 OHMS	1
R2	RES, 1/16W, 0603, 1%, 47 OHMS	1
C6	CAP, 470pF, 10%, 100V, 0603	1
C17	CAP, 33μF, 20%, G CASE	1
C16	CAP, 1.0μF, 100V, 10%, X7R, 1210	1
C8	CAP 10μF 16V TANTALUM	1
C13	CAP, 100.0pF, +/-5%, 0603	1
C1	CAP, 0.8pF, +/-0.05pF, 0603, ATC	1
C2, C9, C10	CAP, 0.7pF, +/-0.05pF, 0603, ATC	3
C4, C11	CAP, 10.0pF,+/-5%, 0603, ATC	2
C5, C12	CAP, 39pF, +/-5%, 0603, ATC	2
C7, C14	CAP, 33000pF, 0805, 100V, X7R	2
J3, J4	CONN SMA STR PANEL JACK RECP	1
J2	HEADER RT>PLZ.1CEN LK 2 POS	1
J1	HEADER RT>PLZ .1CEN LK 5POS	1
-	PCB, RO4350B, Er = 3.48, h = 20 mil	1
-	CGH35030F	1

CGH35030F-AMP Demonstration Amplifier Circuit

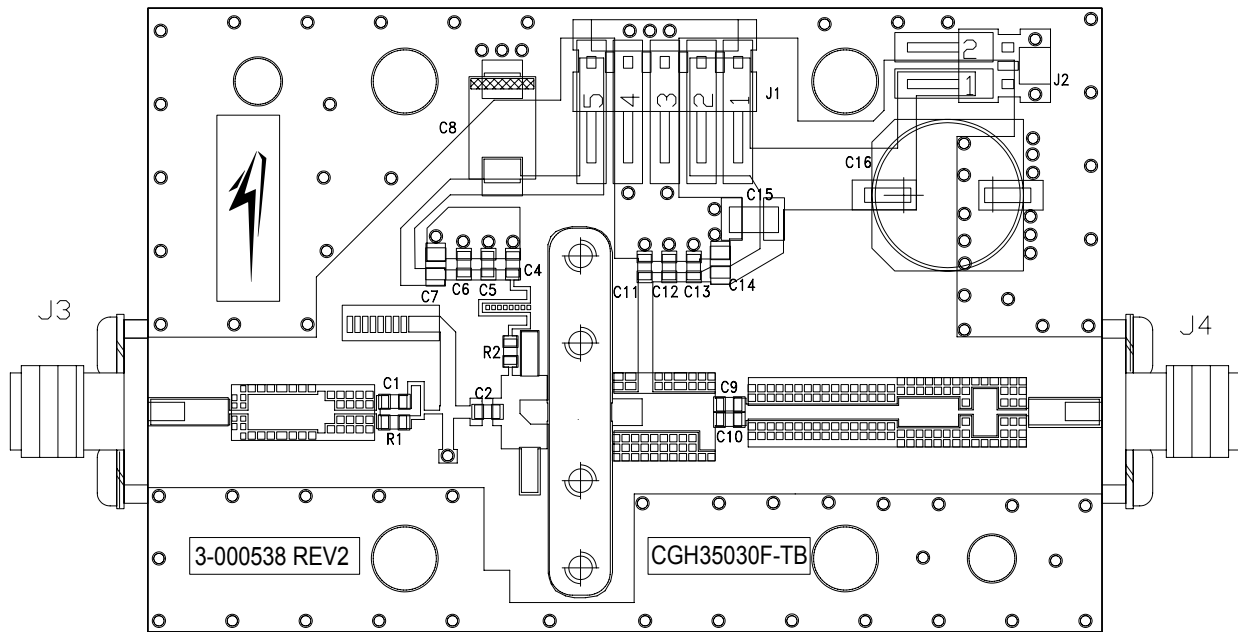




CGH35030F-AMP Demonstration Amplifier Circuit Schematic



CGH35030F-AMP Demonstration Amplifier Circuit Outline



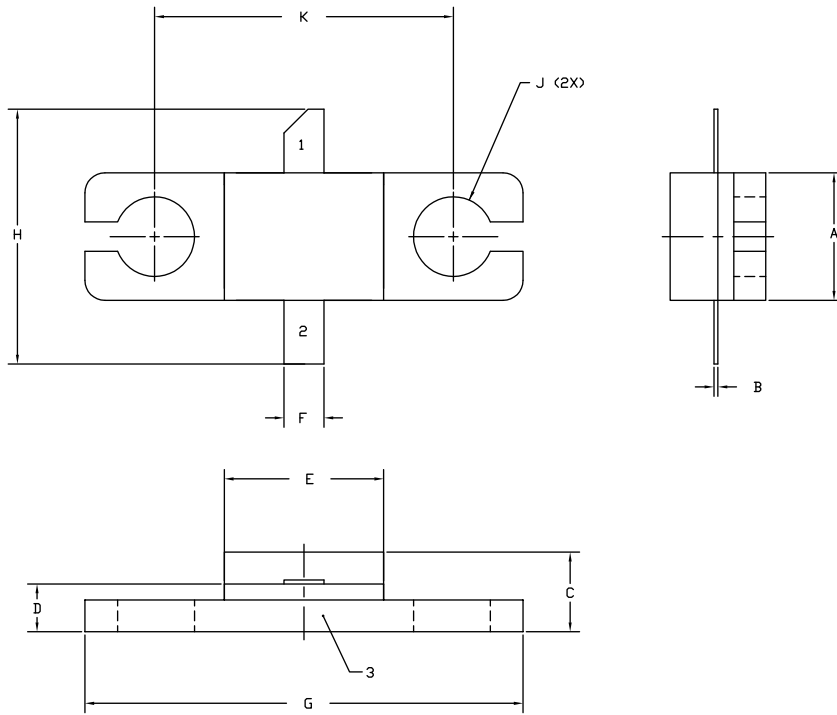


Typical Package S-Parameters for CGH35030F
(Small Signal, $V_{DS} = 28$ V, $I_{DQ} = 120$ mA, angle in degrees)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.909	-152.96	11.93	92.31	0.023	6.73	0.393	-144.30
600 MHz	0.907	-158.23	10.00	87.72	0.023	3.05	0.401	-147.24
700 MHz	0.907	-162.20	8.59	83.77	0.023	0.01	0.410	-149.13
800 MHz	0.907	-165.34	7.51	80.24	0.023	-2.59	0.420	-150.43
900 MHz	0.907	-167.92	6.66	76.99	0.023	-4.90	0.431	-151.37
1.0 GHz	0.908	-170.10	5.98	73.96	0.023	-6.97	0.442	-152.11
1.1 GHz	0.908	-172.00	5.41	71.09	0.022	-8.87	0.454	-152.74
1.2 GHz	0.909	-173.67	4.94	68.35	0.022	-10.62	0.466	-153.31
1.3 GHz	0.910	-175.19	4.53	65.71	0.022	-12.23	0.478	-153.87
1.4 GHz	0.911	-176.58	4.18	63.16	0.022	-13.73	0.490	-154.44
1.5 GHz	0.912	-177.86	3.88	60.70	0.021	-15.13	0.503	-155.02
1.6 GHz	0.913	-179.07	3.61	58.30	0.021	-16.42	0.515	-155.64
1.7 GHz	0.914	-179.79	3.38	55.96	0.020	-17.62	0.528	-156.28
1.8 GHz	0.915	-178.71	3.17	53.68	0.020	-18.72	0.540	-156.96
1.9 GHz	0.916	-177.66	2.98	51.45	0.020	-19.73	0.552	-157.67
2.0 GHz	0.917	-176.65	2.81	49.27	0.019	-20.64	0.564	-158.41
2.1 GHz	0.918	-175.67	2.66	47.14	0.019	-21.45	0.576	-159.17
2.2 GHz	0.919	-174.72	2.52	45.05	0.018	-22.17	0.587	-159.97
2.3 GHz	0.921	-173.78	2.39	43.00	0.018	-22.78	0.598	-160.79
2.4 GHz	0.922	-172.86	2.27	40.99	0.017	-23.28	0.609	-161.62
2.5 GHz	0.923	-171.95	2.16	39.02	0.017	-23.68	0.619	-162.48
2.6 GHz	0.924	-171.05	2.06	37.08	0.016	-23.96	0.629	-163.36
2.7 GHz	0.925	-170.16	1.97	35.18	0.016	-24.11	0.639	-164.24
2.8 GHz	0.926	-169.28	1.89	33.31	0.015	-24.14	0.648	-165.15
2.9 GHz	0.927	-168.41	1.81	31.47	0.015	-24.04	0.657	-166.06
3.0 GHz	0.927	-167.53	1.74	29.66	0.015	-23.79	0.666	-166.98
3.2 GHz	0.929	-165.79	1.61	26.12	0.014	-22.85	0.682	-168.84
3.4 GHz	0.931	-164.05	1.49	22.69	0.013	-21.25	0.697	-170.73
3.6 GHz	0.932	-162.30	1.39	19.35	0.012	-18.94	0.711	-172.64
3.8 GHz	0.933	-160.54	1.30	16.10	0.012	-15.90	0.724	-174.56
4.0 GHz	0.934	-158.76	1.23	12.92	0.011	-12.15	0.735	-176.49
4.2 GHz	0.935	-156.96	1.16	9.80	0.011	-7.76	0.746	-178.43
4.4 GHz	0.936	-155.14	1.10	6.75	0.011	-2.91	0.755	-179.63
4.6 GHz	0.937	-153.27	1.04	3.74	0.011	2.16	0.764	-177.67
4.8 GHz	0.937	-151.38	0.99	0.78	0.011	7.15	0.772	-175.70
5.0 GHz	0.938	-149.44	0.95	-2.15	0.012	11.82	0.779	-173.71
5.2 GHz	0.938	-147.46	0.91	-5.05	0.013	15.96	0.786	-171.71
5.4 GHz	0.938	-145.42	0.88	-7.92	0.014	19.45	0.791	-169.69
5.6 GHz	0.938	-143.34	0.85	-10.79	0.015	22.27	0.796	-167.65
5.8 GHz	0.938	-141.19	0.82	-13.65	0.016	24.42	0.801	-165.58
6.0 GHz	0.937	-138.98	0.79	-16.50	0.017	25.96	0.805	-163.48



Product Dimensions CGH35030F (Package Type — 440166)



NOTES:

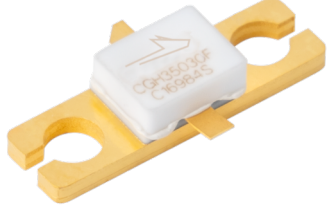
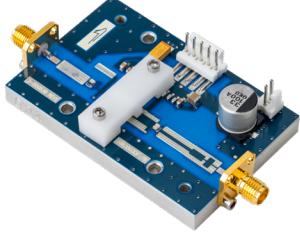
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.
5. ALL PLATED SURFACES ARE NI/AU

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.155	0.165	3.94	4.19
B	0.004	0.006	0.10	0.15
C	0.115	0.135	2.92	3.43
D	0.057	0.067	1.45	1.70
E	0.195	0.205	4.95	5.21
F	0.045	0.055	1.14	1.40
G	0.545	0.555	13.84	14.09
H	0.280	0.360	7.11	9.14
J	∅ .100		2.54	
K	0.375		9.53	

- PIN 1. GATE
 PIN 2. DRAIN
 PIN 3. SOURCE



Product Ordering Information

Order Number	Description	Unit of Measure	Image
CGH35030F	GaN HEMT	Each	 A white GaN HEMT device is mounted on a yellow plastic carrier. The carrier has two semi-circular cutouts on the sides. The device has the Wolfstreak logo and 'CGH35030F' printed on it.
CGH35030F-AMP	Test board with GaN HEMT installed	Each	 A blue printed circuit board (PCB) with various electronic components, including a white GaN HEMT device, a silver capacitor, and several connectors. It is a test board for the GaN HEMT device.

**For more information, please contact:**

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